

## ABSTRACT OF THE DISCLOSURE

1       A semiconductor device is disclosed including a transistor that may have desired  
2 characteristics due to a silicon nitride film that may prevent carbon from diffusing to a silicon  
3 substrate. The semiconductor device (60) may include a device structure having an  
4 insulating film formed from gas containing carbon. A silicon nitride film may be formed  
5 between the insulating film and a transistor formation region in the silicon substrate for  
6 preventing carbon from diffusing to the silicon substrate.

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